

What is claimed is:

1. A method of erasing an electrically nonvolatile memory cell that includes a source region, a drain region, a floating gate electrode and a control gate electrode to which an erase signal is applied, the method comprising:

5 applying a source bias voltage to the source region;
 applying a drain bias voltage to the drain region; and
 applying a frequency/time domain based voltage signal to the control gate electrode of the cell as the erase signal.

10 2. A method as in claim 1, and wherein the frequency/time domain based voltage signal comprises a pulsed signal.

 3. A method as in claim 1, and wherein the frequency/time domain based voltage signal comprises a radio frequency signal.

15